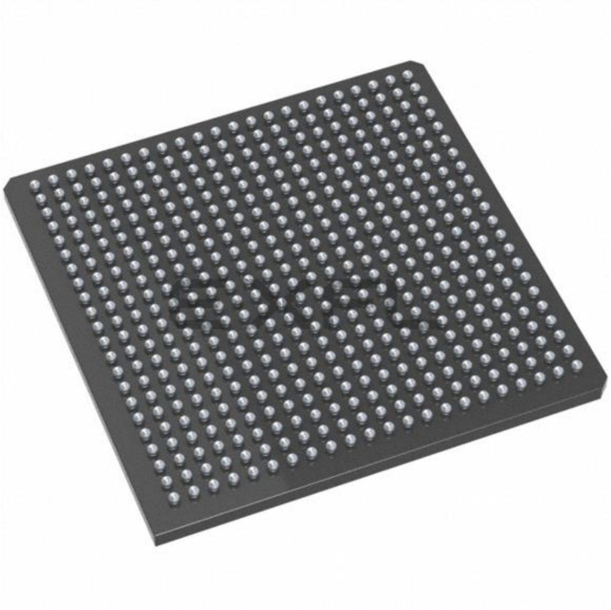

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 154K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	484-BFBGA, FCBGA
Supplier Device Package	484-FCBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu3cg-l2sbva484e

Table 1: **Absolute Maximum Ratings(1)** ***(Cont'd)***

Symbol	Description	Min	Max	Units
V_{CCO_PSDDR}	PS DDR I/O supply voltage.	–0.500	1.650	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	–0.500	2.000	V
V_{CCO_PSIO}	PS I/O supply.	–0.500	3.630	V
V_{PSIN}(2)	PS I/O input voltage.	–0.500	V_{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	–0.500	V_{CCO_PSDDR} + 0.550	V
V_{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	–0.500	2.000	V
Programmable Logic (PL)				
V_{CCINT}	Internal supply voltage.	–0.500	1.000	V
V_{CCINT_IO}(3)	Internal supply voltage for the I/O banks.	–0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	–0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	–0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	–0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	–0.500	2.000	V
V_{CCAUX_IO}(4)	Auxiliary supply voltage for the I/O banks.	–0.500	2.000	V
V_{REF}	Input reference voltage.	–0.500	2.000	V
V_{IN}(2)(5)(7)	I/O input voltage for HD I/O banks.(6)	–0.550	V_{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	–0.550	V_{CCO} + 0.550	V
I_{DC}	Available output current at the pad.	–20	20	mA
I_{RMS}	Available RMS output current at the pad.	–20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	–0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	–0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	–0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	–0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	–0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	–0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.(8)	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.(9)	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.(10)	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.[12]	–	260	°C
T_j	Maximum junction temperature.[12]	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
I_{CC_PSBATT}[4][5]	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}[6]	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks[8] (measured per JEDEC specification)					
R[9]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–10%[7]	40	+10%[7]	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–10%[7]	48	+10%[7]	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–10%[7]	60	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%[7]	40	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%[7]	48	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%[7]	60	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%[7]	120	+10%[7]	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%[7]	240	+10%[7]	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R[9]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R[9]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 17: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM} (V)[1]			V_{ID}(V)[2]			V_{ILHS}[3]	V_{IHHS}[3]	V_{OCM}(V)[4]			V_{OD}(V)[5]		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS[8]	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
LVPECL	0.300	1.200	1.425	0.100	0.350	0.600	–	–	–	–	–	–	–	–
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
SLVS_400_25	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS[9]	0.070	–	0.330	0.070	–	–	–0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
4. V_{OCM} is the output common mode voltage.
5. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
6. LVDS_25 is specified in Table 23.
7. LVDS is specified in Table 24.
8. Only the SUB_LVDS receiver is supported in HD I/O banks.
9. High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 18: **Complementary Differential SelectIO DC Input and Output Levels for HD I/O Banks**

I/O Standard	V_{ICM} (V)[1]			V_{ID} (V)[2]		V_{OL} (V)[3]	V_{OH} (V)[4]	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL135_II	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL15_II	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.0	–8.0
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the Vivado® Design Suite as outlined in Table 25.

Table 25: **Speed Specification Version By Device**

2017.1	Device
1.08	XCZU4CG, XCZU4EG, XCZU4EV, XCZU5CG, XCZU5EG, XCZU5EV, XCZU11EG
1.10	XCZU2CG, XCZU2EG, XCZU3CG, XCZU3EG, XCZU6CG, XCZU6EG, XCZU7CG, XCZU7EG, XCZU7EV, XCZU9CG, XCZU9EG, XCZU15EG, XCZU17EG, XCZU19EG

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Zynq UltraScale+ MPSoC.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU2EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU4CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

PS Switching Characteristics

PS Clocks

Table 34: **PS Reference Clock Requirements**[(1)]

Symbol	Description	Min	Typ	Max	Units
$T_{RMSJPSCLK}$	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
$T_{PJPSCLK}$	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
$T_{DCPSCLK}$	PS_REF_CLK duty cycle.	45	–	55	%
$T_{RFPSCLK}$	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F_{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

1. The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: **PS RTC Crystal Requirements**[(1)]

Symbol	Description	Min	Typ	Max	Units
F_{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T_{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C_{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R_{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C_{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

1. Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C_1 and C_2 capacitance = 21 pF.

Table 36: **PS PLL Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{LOCKPSPLL}$	PLL maximum lock time.	100	100	100	µs
$F_{PSPLLMAX}$	PLL maximum output frequency.	1600	1600	1600	MHz
$F_{PSPLLMIN}$	PLL minimum output frequency.	750	750	750	MHz
$F_{PSPLLVCOMAX}$	PLL maximum VCO frequency.	3000	3000	3000	MHz
$F_{PSPLLVCOMIN}$	PLL minimum VCO frequency.	1500	1500	1500	MHz

PS I2C Controller Interface

Table 47: **I2C Interface**[1]

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	µs
$T_{I2CFCKH}$	SCL High time.	0.6	–	µs
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	µs
$T_{I2CSCKH}$	SCL High time.	4.0	–	µs
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SPI Controller Interface

Table 48: **SPI Interfaces**(1)

Symbol	Description	Min	Max	Units
SPI Master Interface				
$T_{DCMSPICLK}$	SPI master mode clock duty cycle.	45	55	%
$T_{MSPISSSCLK}$	Slave select asserted to first active clock edge.	1(2)	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{MSPISCLKSS}$	Last active clock edge to slave select deasserted.	1(2)	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{MSPIDCK}$	Input setup time for MISO.	–2.0	–	ns
$T_{MSPICKD}$	Input hold time for MISO.	0.3	–	$F_{MSPICLK}$ cycles
$T_{MSPICKO}$	MOSI and slave select clock to out delay.	–2.0	5.0	ns
$F_{MSPICLK}$	SPI master device clock frequency.	–	50	MHz
$F_{SPI\_REF\_CLK}$	SPI reference clock frequency.	–	200	MHz
SPI Slave Interface				
$T_{SSPISSSCLK}$	Slave select asserted to first active clock edge.	2	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{SSPISCLKSS}$	Last active clock edge to slave select deasserted.	2	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{SSPIDCK}$	Input setup time for MOSI.	5.0	–	ns
$T_{SSPICKD}$	Input hold time for MOSI.	1	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{SSPICKO}$	MISO clock to out delay.	0.0	13.0	ns
$F_{SSPICLK}$	SPI slave mode device clock frequency.	–	25	MHz
$F_{SPI\_REF\_CLK}$	SPI reference clock frequency.	–	200	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 30 pF load.
2. Valid when two SPI_REF_CLK delays are programmed between CS and CLK for $T_{MSPISSSCLK}$, and between CLK and CS for $T_{MSPISCLKSS}$ in the SPI delay_reg0 register.

PS CAN Controller Interface

Table 49: **CAN Interface**(1)

Symbol	Description	Min	Max	Units
$T_{PWCANRX}$	Receive pulse width.	1.0	–	µs
$T_{PWCANTX}$	Transmit pulse width.	1.0	–	µs
$F_{CAN\_REF\_CLK}$	Internally sourced CAN reference clock frequency.	–	100	MHz
	Externally sourced CAN reference clock frequency.	–	40	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Table 72: **MIPI D-PHY Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3(1)	-2(1)	-1	-2	-1	
MIPI D-PHY transmitter or receiver.	HP	1500	1500	1260	1260	1260	Mb/s

Notes:

1. In the SBVA484 package, the data rate is 1260 Mb/s.

Table 73: **LVDS Native-Mode 1000BASE-X Support(1)**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages				
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	-1
1000BASE-X	HP	Yes				

Notes:

1. 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

Table 74 provides the maximum data rates for applicable memory standards using the Zynq UltraScale+ MPSoC memory PHY. Refer to Memory Interfaces for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* (UG583), electrical analysis, and characterization of the system.

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces**

Memory Standard	Package(1)	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR4	All FFV packages and FBVB900	Single rank component	2666	2666	2400	2400	2133	Mb/s
		1 rank DIMM(2)(3)(4)	2400	2400	2133	2133	1866	Mb/s
		2 rank DIMM(2)(5)	2133	2133	1866	1866	1600	Mb/s
		4 rank DIMM(2)(6)	1600	1600	1333	1333	N/A	Mb/s
	SFVC784	Single rank component	2400	2400	2133	2133	1866	Mb/s
		1 rank DIMM(2)(3)	2133	2133	1866	1866	1600	Mb/s
		2 rank DIMM(2)(5)	1866	1866	1600	1600	1600	Mb/s
DDR3	All FFV packages and FBVB900	Single rank component	2133	2133	2133	2133	1866	Mb/s
		1 rank DIMM(2)(3)	1866	1866	1866	1866	1600	Mb/s
		2 rank DIMM(2)(5)	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM(2)(6)	1066	1066	1066	1066	800	Mb/s
	SFVC784	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1600	Mb/s
		2 rank DIMM(2)(5)	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM(2)(6)	1066	1066	1066	1066	800	Mb/s

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces *(Cont'd)***

Memory Standard	Package[1]	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR3L	All FFV packages and FBVB900	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM[2][3]	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM[2][5]	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM[2][6]	800	800	800	800	606	Mb/s
	SFVC784	Single rank component	1600	1600	1600	1600	1600	Mb/s
		1 rank DIMM[2][3]	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM[2][5]	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM[2][6]	800	800	800	800	606	Mb/s
QDR II+	All	Single rank component[7]	633	633	600	600	550	MHz
RLDRAM 3	All FFV packages and FBVB900	Single rank component	1200	1200	1066	1066	933	MHz
	SFVC784	Single rank component	1066	1066	933	933	800	MHz
QDR IV XP	All	Single rank component	1066	1066	1066	933	933	MHz
LPDDR3	All	Single rank component	1600	1600	1600	1600	1600	Mb/s

Notes:

1. The SBVA484 and SFVA625 packages do not support the PL memory interfaces.
2. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
3. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
4. For the DDR4 DDP components at -3 and -2 speed grades and V_{CCINT} = 0.85V, the maximum data rate is 2133 Mb/s for six or more DDP devices. For five or less DDP devices, use the single rank DIMM data rates for the -3 and -2 speed grades at 0.85V.
5. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
6. Includes: 2 rank 2 slot, 4 rank 1 slot.
7. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

Table 76: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{\text{INBUF\_DELAY\_PAD\_I}}$					$T_{\text{OUTBUF\_DELAY\_O\_PAD}}$					$T_{\text{OUTBUF\_DELAY\_TD\_PAD}}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
SSTL135_DCI_S	0.366	0.366	0.399	0.366	0.399	0.746	0.746	0.799	0.746	0.799	0.829	0.829	0.893	0.829	0.893	ns
SSTL135_F	0.378	0.378	0.399	0.378	0.399	0.408	0.408	0.428	0.408	0.428	0.528	0.528	0.561	0.528	0.561	ns
SSTL135_M	0.378	0.378	0.399	0.378	0.399	0.555	0.555	0.585	0.555	0.585	0.641	0.641	0.679	0.641	0.679	ns
SSTL135_S	0.378	0.378	0.399	0.378	0.399	0.772	0.772	0.823	0.772	0.823	0.827	0.827	0.878	0.827	0.878	ns
SSTL15_DCI_F	0.402	0.402	0.417	0.402	0.417	0.412	0.412	0.429	0.412	0.429	0.531	0.531	0.563	0.531	0.563	ns
SSTL15_DCI_M	0.402	0.402	0.417	0.402	0.417	0.553	0.553	0.583	0.553	0.583	0.645	0.645	0.685	0.645	0.685	ns
SSTL15_DCI_S	0.402	0.402	0.417	0.402	0.417	0.768	0.768	0.822	0.768	0.822	0.847	0.847	0.912	0.847	0.912	ns
SSTL15_F	0.371	0.371	0.400	0.371	0.400	0.408	0.408	0.428	0.408	0.428	0.530	0.530	0.556	0.530	0.556	ns
SSTL15_M	0.371	0.371	0.400	0.371	0.400	0.554	0.554	0.585	0.554	0.585	0.639	0.639	0.677	0.639	0.677	ns
SSTL15_S	0.371	0.371	0.400	0.371	0.400	0.767	0.767	0.817	0.767	0.817	0.813	0.813	0.867	0.813	0.867	ns
SSTL18_I_DCI_F	0.329	0.329	0.336	0.329	0.336	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
SSTL18_I_DCI_M	0.329	0.329	0.336	0.329	0.336	0.554	0.554	0.585	0.554	0.585	0.644	0.644	0.683	0.644	0.683	ns
SSTL18_I_DCI_S	0.329	0.329	0.336	0.329	0.336	0.762	0.762	0.818	0.762	0.818	0.837	0.837	0.899	0.837	0.899	ns
SSTL18_I_F	0.316	0.316	0.337	0.316	0.337	0.454	0.454	0.476	0.454	0.476	0.578	0.578	0.608	0.578	0.608	ns
SSTL18_I_M	0.316	0.316	0.337	0.316	0.337	0.571	0.571	0.603	0.571	0.603	0.652	0.652	0.692	0.652	0.692	ns
SSTL18_I_S	0.316	0.316	0.337	0.316	0.337	0.782	0.782	0.835	0.782	0.835	0.816	0.816	0.870	0.816	0.870	ns
SUB_LVDS	0.539	0.539	0.620	0.539	0.620	0.660	0.660	0.692	0.660	0.692	969.863	969.863	969.863	969.863	969.863	ns

IOB 3-state Output Switching Characteristics

Table 77 specifies the values of $T_{\text{OUTBUF\_DELAY\_TE\_PAD}}$ and $T_{\text{INBUF\_DELAY\_IBUFDIS\_O}}$. $T_{\text{OUTBUF\_DELAY\_TE\_PAD}}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{\text{INBUF\_DELAY\_IBUFDIS\_O}}$ is the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than $T_{\text{OUTBUF\_DELAY\_TE\_PAD}}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the internal IN_TERM termination turn-off time is always faster than $T_{\text{OUTBUF\_DELAY\_TE\_PAD}}$ when the INTERMDISABLE pin is used.

Table 77: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$T_{\text{OUTBUF\_DELAY\_TE\_PAD}}$	T input to pad high-impedance for HD I/O banks	6.318	6.318	6.369	6.318	6.369	ns
	T input to pad high-impedance for HP I/O banks	5.330	5.330	5.341	5.330	5.341	ns
$T_{\text{INBUF\_DELAY\_IBUFDIS\_O}}$	IBUF turn-on time from IBUFDISABLE to O output for HD I/O banks	2.266	2.266	2.430	2.266	2.430	ns
	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	0.936	0.936	1.037	0.936	1.037	ns

Input Delay Measurement Methodology

Table 78 shows the test setup parameters used for measuring input delay.

Table 78: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L(1)(2)	V_H(1)(2)	V_{MEAS}(1)(4)(6)	V_{REF}(1)(3)(5)
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	–
LVCMOS, LVDCI, HSLVDCI, 1.5V	LVCMOS15, LVDCI_15, HSLVDCI_15	0.1	1.4	0.75	–
LVCMOS, LVDCI, HSLVDCI, 1.8V	LVCMOS18, LVDCI_18, HSLVDCI_18	0.1	1.7	0.9	–
LVCMOS, 2.5V	LVCMOS25	0.1	2.4	1.25	–
LVCMOS, 3.3V	LVCMOS33	0.1	3.2	1.65	–
LVTTL, 3.3V	LVTTL	0.1	3.2	1.65	–
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	V_{REF} – 0.2875	V_{REF} + 0.2875	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
SSTL18, class I and II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
POD10, 1.0V	POD10	V_{REF} – 0.2	V_{REF} + 0.2	V_{REF}	0.7
POD12, 1.2V	POD12	V_{REF} – 0.24	V_{REF} + 0.24	V_{REF}	0.84
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_HSUL, 1.2V	DIFF_HSUL_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL, 1.2V	DIFF_SSTL12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	0.675 – 0.2875	0.675 + 0.2875	0(6)	–
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_SSTL18_I, DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_POD10, 1.0V	DIFF_POD10	0.5 – 0.2	0.5 + 0.2	0(6)	–
DIFF_POD12, 1.2V	DIFF_POD12	0.6 – 0.25	0.6 + 0.25	0(6)	–
LVDS (low-voltage differential signaling), 1.8V	LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
LVDS_25, 2.5V	LVDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–

Device Pin-to-Pin Output Parameter Guidelines

The pin-to-pin numbers in Table 87 through Table 89 are based on the clock root placement in the center of the device. The actual pin-to-pin values will vary if the root placement selected is different. Consult the Vivado Design Suite timing report for the actual pin-to-pin values.

Table 87: **Global Clock Input to Output Delay Without MMCM (Near Clock Region)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM.								
T_{ICKOF}	Global clock input and output flip-flop *without* MMCM (near clock region).	XCZU2	N/A	4.90	5.28	5.35	5.61	ns
		XCZU3	N/A	4.90	5.28	5.35	5.61	ns
		XCZU4	4.89	5.83	6.36	6.00	6.79	ns
		XCZU5	4.89	5.83	6.36	6.00	6.79	ns
		XCZU6	5.00	5.91	6.35	6.66	7.09	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.00	5.91	6.35	6.66	7.09	ns
		XCZU11	5.82	6.96	7.61	7.19	8.36	ns
		XCZU15	5.15	6.09	6.55	6.90	7.38	ns
		XCZU17	5.72	6.90	7.40	7.62	8.07	ns
		XCZU19	5.72	6.90	7.40	7.62	8.07	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 88: Global Clock Input to Output Delay Without MMCM (Far Clock Region)

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM.								
T_{ICKOF_FAR}	Global clock input and output flip-flop *without* MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: Global Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
$T_{ICKOFMMCMCC}$	Global clock input and output flip-flop *with* MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
		XCZU19	2.44	2.44	2.66	3.19	3.17	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

GTH Transceiver Switching Characteristics

Consult the *UltraScale Architecture GTH Transceiver User Guide* (UG576) for further information.

Table 97: **GTH Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
F_{GTHMAX}	GTH maximum line rate.		16.375[1]		16.375[1]		12.5		12.5		10.3125		Gb/s
F_{GTHMIN}	GTH minimum line rate.		0.5		0.5		0.5		0.5		0.5		Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTHCRANGE}$	CPLL line rate range[2].	1	4	12.5	4	12.5	4	8.5	4	8.5	4	8.5	Gb/s
		2	2	6.25	2	6.25	2	4.25	2	4.25	2	4.25	Gb/s
		4	1	3.125	1	3.125	1	2.125	1	2.125	1	2.125	Gb/s
		8	0.5	1.5625	0.5	1.5625	0.5	1.0625	0.5	1.0625	0.5	1.0625	Gb/s
		16	N/A										Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTHQRANGE1}$	QPLL0 line rate range[3].	1	9.8	16.375	9.8	16.375	9.8	12.5	9.8	12.5	9.8	10.3125	Gb/s
		2	4.9	8.1875	4.9	8.1875	4.9	8.15	4.9	8.1875	4.9	8.15	Gb/s
		4	2.45	4.0938	2.45	4.0938	2.45	4.075	2.45	4.0938	2.45	4.075	Gb/s
		8	1.225	2.0469	1.225	2.0469	1.225	2.0375	1.225	2.0469	1.225	2.0375	Gb/s
		16	0.6125	1.0234	0.6125	1.0234	0.6125	1.0188	0.6125	1.0234	0.6125	1.0188	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTHQRANGE2}$	QPLL1 line rate range[4].	1	8.0	13.0	8.0	13.0	8.0	12.5	8.0	12.5	8.0	10.3125	Gb/s
		2	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	Gb/s
		4	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	Gb/s
		8	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	Gb/s
		16	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{CPLLRANGE}$	CPLL frequency range.		2	6.25	2	6.25	2	4.25	2	4.25	2	4.25	GHz
$F_{QPLL0RANGE}$	QPLL0 frequency range.		9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	GHz
$F_{QPLL1RANGE}$	QPLL1 frequency range.		8	13	8	13	8	13	8	13	8	13	GHz

Notes:

1. GTH transceiver line rates in the SFVC784 package support data rates up to 12.5 Gb/s.
2. The values listed are the rounded results of the calculated equation (2 x CPLL_Frequency)/Output_Divider.
3. The values listed are the rounded results of the calculated equation (QPLL0_Frequency)/Output_Divider.
4. The values listed are the rounded results of the calculated equation (QPLL1_Frequency)/Output_Divider.

Table 98: **GTH Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	All Speed Grades	Units
$F_{GTHDRPCLK}$	GTHDRPCLK maximum frequency.	250	MHz

GTY Transceiver Switching Characteristics

Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further information.

Table 109: **GTY Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
F_{GTYMAX}	GTY maximum line rate		32.75		28.21		25.7813		28.21		12.5		Gb/s
F_{GTYMIN}	GTY minimum line rate		0.5		0.5		0.5		0.5		0.5		Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYCRANGE}$	CPLL line rate range[1]	1	4.0	12.5	4.0	12.5	4.0	8.5	4.0	12.5	4.0	8.5	Gb/s
		2	2.0	6.25	2.0	6.25	2.0	4.25	2.0	6.25	2.0	4.25	Gb/s
		4	1.0	3.125	1.0	3.125	1.0	2.125	1.0	3.125	1.0	2.125	Gb/s
		8	0.5	1.5625	0.5	1.5625	0.5	1.0625	0.5	1.5625	0.5	1.0625	Gb/s
		16	N/A										Gb/s
		32	N/A										Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYQRANGE1}$	QPLL0 line rate range[2]	1	19.6	32.75	19.6	28.21	19.6	25.7813	19.6	28.21	N/A		Gb/s
		1	9.8	16.375	9.8	16.375	9.8	12.5	9.8	16.375	9.8	12.5	Gb/s
		2	4.9	8.1875	4.9	8.1875	4.9	8.1875	4.9	8.1875	4.9	8.1875	Gb/s
		4	2.45	4.0938	2.45	4.0938	2.45	4.0938	2.45	4.0938	2.45	4.0938	Gb/s
		8	1.225	2.0469	1.225	2.0469	1.225	2.0469	1.225	2.0469	1.225	2.0469	Gb/s
		16	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYQRANGE2}$	QPLL1 line rate range[3]	1	16.0	26.0	16.0	26.0	19.6	25.7813	16.0	26.0	N/A		Gb/s
		1	8.0	13.0	8.0	13.0	8.0	12.5	8.0	13.0	8.0	12.5	Gb/s
		2	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	Gb/s
		4	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	Gb/s
		8	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	Gb/s
		16	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{CPLLRANGE}$	CPLL frequency range		2.0	6.25	2.0	6.25	2.0	4.25	2.0	6.25	2.0	4.25	GHz
$F_{QPLL0RANGE}$	QPLL0 frequency range		9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	GHz
$F_{QPLL1RANGE}$	QPLL1 frequency range		8.0	13.0	8.0	13.0	8.0	13.0	8.0	13.0	8.0	13.0	GHz

Notes:

1. The values listed are the rounded results of the calculated equation (2 x CPLL_Frequency)/Output_Divider.
2. The values listed are the rounded results of the calculated equation (2 x QPLL0_Frequency)/Output_Divider.
3. The values listed are the rounded results of the calculated equation (2 x QPLL1_Frequency)/Output_Divider.

Table 110: **GTY Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	All Speed Grades	Units
$F_{GTYDRPCLK}$	GTYDRPCLK maximum frequency.	250	MHz

Table 111: **GTY Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range.		60	–	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 112: **GTY Transceiver Reference Clock Oscillator Selection Phase Noise Mask(1)**

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency =625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
$CPLL_{REFCLKMASK}$	CPLL reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
		50 MHz	–	–	–144	

Notes:

1. For reference clock frequencies not in this table, use the phase-noise mask for the nearest reference clock frequency.
2. This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Integrated Interface Block for 100G Ethernet MAC and PCS

More information and documentation on solutions using the integrated 100 Gb/s Ethernet block can be found at UltraScale+ Integrated 100G Ethernet MAC/PCS. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC.

Table 121: **Maximum Performance for 100G Ethernet Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2(1)	-1	-2	-1(2)	
F_{TX_CLK}	Transmit clock	390.625	390.625	322.223	322.223	322.223	MHz
F_{RX_CLK}	Receive clock	390.625	390.625	322.223	322.223	322.223	MHz
$F_{RX\_SERDES\_CLK}$	Receive serializer/deserializer clock	390.625	390.625	322.223	322.223	322.223	MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	250.00	250.00	250.00	MHz

Notes:

1. The maximum clock frequency of 390.625 MHz only applies to the CAUI-10 interface. The maximum clock frequency for the CAUI-4 interface is 322.223 MHz.
2. The CAUI-4 interface is not supported by -1L speed grade devices where V_{CCINT}=0.72V.

Integrated Interface Block for PCI Express Designs

More information and documentation on solutions for PCI Express designs can be found at PCI Express. The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include this block.

Table 122: **Maximum Performance for PCI Express Designs(1)(2)**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$F_{PIPECLK}$	Pipe clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
$F_{CORECLK}$	Core clock maximum frequency.	500.00	500.00	500.00	250.00	250.00	MHz
F_{DRPCLK}	DRP clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
$F_{MCAPCLK}$	MCAP clock maximum frequency.	125.00	125.00	125.00	125.00	125.00	MHz

Notes:

1. PCI Express Gen4 operation is supported for x1, x2, x4, and x8 widths.
2. PCI Express Gen4 operation is supported in -3E, -2E, and -2I speed grades.

Video Codec Performance

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoC EV devices that include the Video Codec unit (VCU).

Table 123: **VCU Performance**

Description	**Speed Grade and V_{CCINT} Operating Voltages**					**Units**
	0.90V	**0.85V**		**0.72V**		
	-3	**-2**	**-1**	**-2**	**-1**	
Video Codec decoder block maximum frequency (H.264/5 10-bit 4:2:2)	667	667	667	667	667	MHz

PL System Monitor Specifications

Table 124: **PL SYSMON Specifications**

Parameter	**Symbol**	**Comments/Conditions**	**Min**	**Typ**	**Max**	**Units**
V_{CCADC} = 1.8V ±3%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 5.2 MHz, T_j = –40°C to 100°C, typical values at T_j = 40°C						
ADC Accuracy(1)						
Resolution			10	–	–	Bits
Integral nonlinearity(2)	INL		–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset error		Offset calibration enabled	–	–	±2	LSBs
Gain error			–	–	±0.4	%
Sample rate			–	–	0.2	MS/s
RMS code noise		External 1.25V reference	–	–	1	LSBs
		On-chip reference	–	1	–	LSBs
ADC Accuracy at Extended Temperatures						
Resolution		T_j = –55°C to 125°C	10	–	–	Bits
Integral nonlinearity(2)	INL	T_j = –55°C to 125°C	–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic (T_j = –55°C to 125°C)	–	–	±1	
Analog Inputs(2)						
ADC input ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V